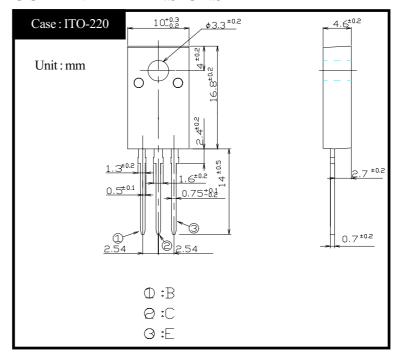
Switching Power Transistor

2SA1600 (TP12T4)

-12A PNP

OUTLINE DIMENSIONS



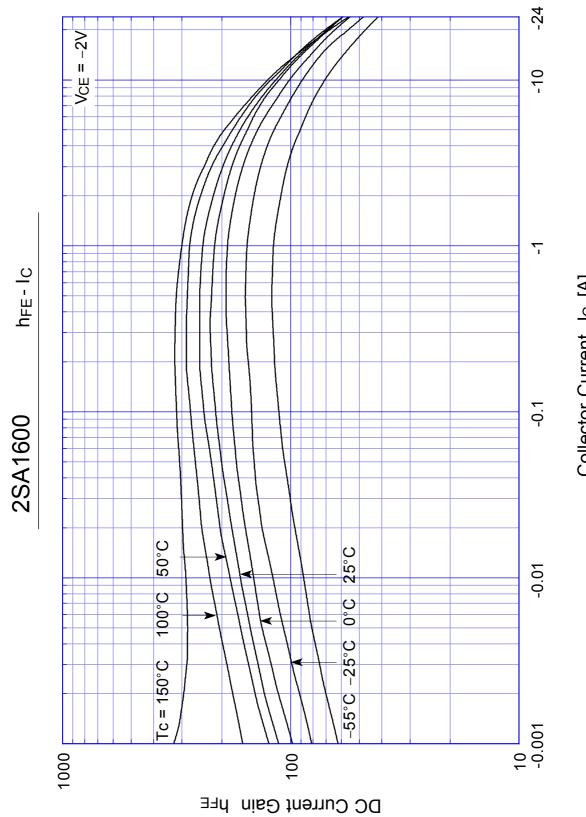
RATINGS

Absolute Maximum Ratings

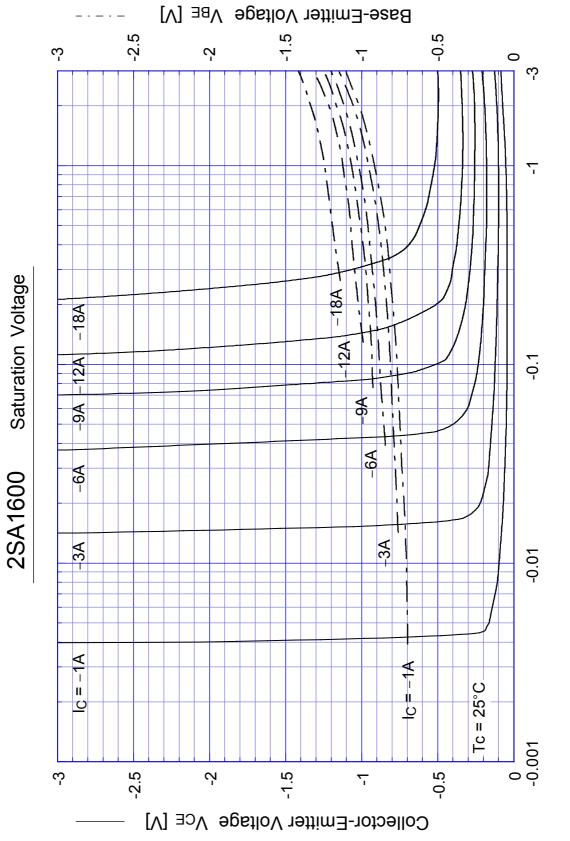
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-55~150	$^{\circ}\!\mathbb{C}$
Junction Temperature	Tj		150	$^{\circ}\!\mathbb{C}$
Collector to Base Voltage	V_{cbo}		-60	V
Collector to Emitter Voltage	V_{ceo}		-40	V
Emitter to Base Voltage	V_{EBO}		-7	V
Collector Current DC	I _C		-12	Α
Collector Current Peak	I _{CP}		-24	Α
Base Current DC	\mathbf{I}_{B}		-2	Α
Base Current Peak	\mathbf{I}_{BP}		-3	Α
Total Transistor Dissipation	P_{T}	$Tc = 25^{\circ}C$	30	W
Dielectric Strength	Vdis	Terminal to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.3N·m)	0.5	N∙m

● Electrical Characteristics (Tc=25°C)

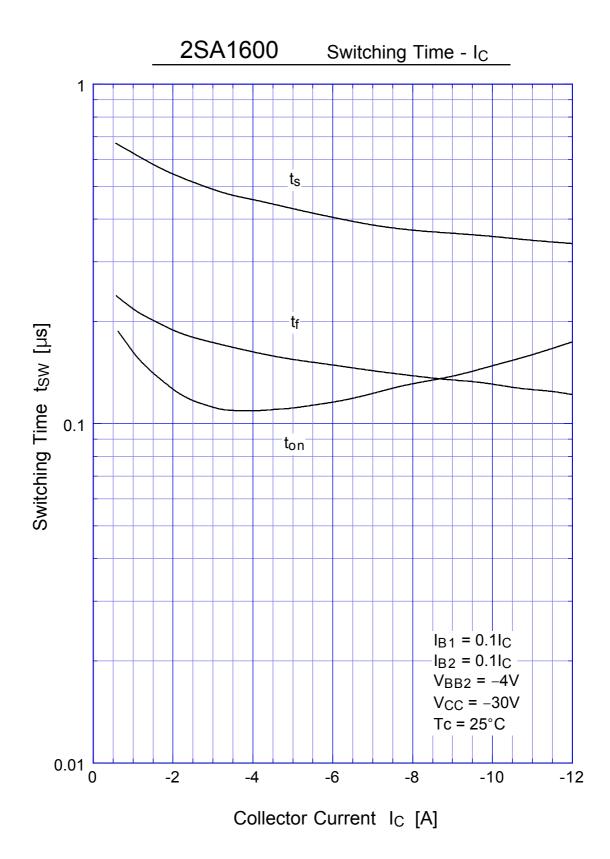
Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	$ m V_{CEO}(sus)$	$I_{C} = -0.1A$	Min -40	V
Collector Cutoff Current	$I_{ extsf{CBO}}$	At rated Voltage	Max −0.1	mA
	$I_{ extsf{C} ext{EO}}$		Max −0.1	
Emitter Cutoff Current	$\mathbf{I}_{\mathrm{EBO}}$	At rated Voltage	Max −0.1	mΑ
DC Current Gain	$\mathrm{h_{FE}}$	$V_{CE} = -2V$, $I_C = -6A$	M in 70	
Collector to Emitter Saturation Voltage	$V_{ extsf{CE}}(extsf{sat})$	$I_{C} = -6A$	Max −0.3	V
Base to Emitter Saturation Voltage	$ m V_{BE}(sat)$	$I_{\rm B} = -0.3$ A	Max −1.2	V
Thermal Resistance	θ jc	Junction to case	Max 4.16	°C/W
Transition Frequency	f_{T}	$V_{CE} = -10V, I_{C} = -1.2A$	TYP 50	$\mathbf{M} \mathrm{Hz}$
Turn on Time	ton		Max 0.3	
		$I_{C} = -6A$		
Storage Time	ts	$I_{B1} = -0.6A, I_{B2} = -0.6A$	Max 1.5	μ s
		R_L = 5 Ω , V_BB2 = -4 V		
Fall Time	tf		Max 0.5	

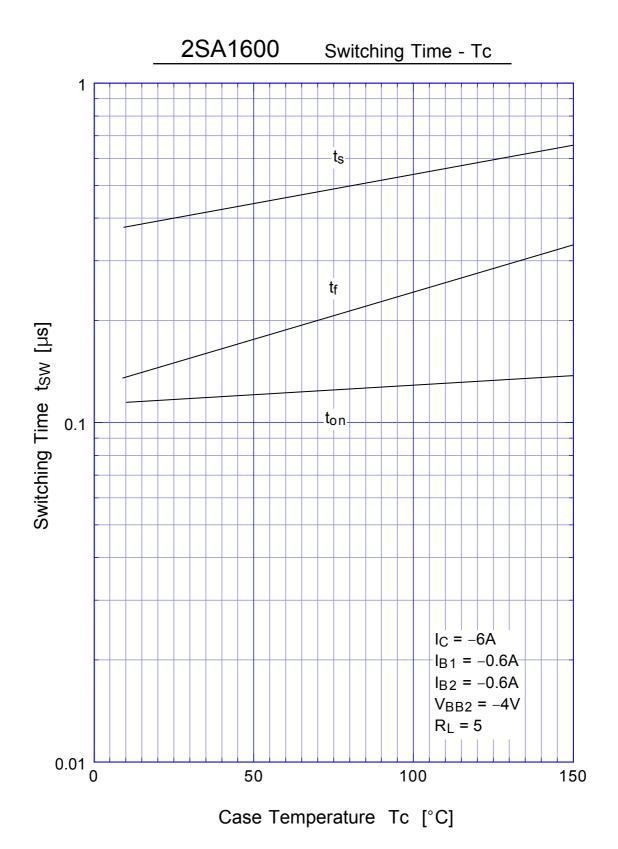


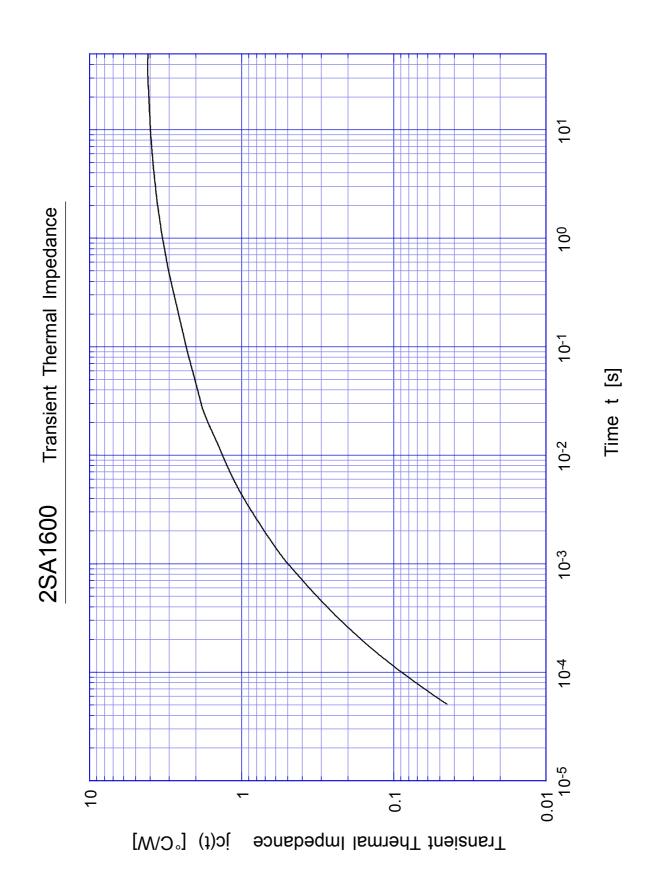
Collector Current Ic [A]

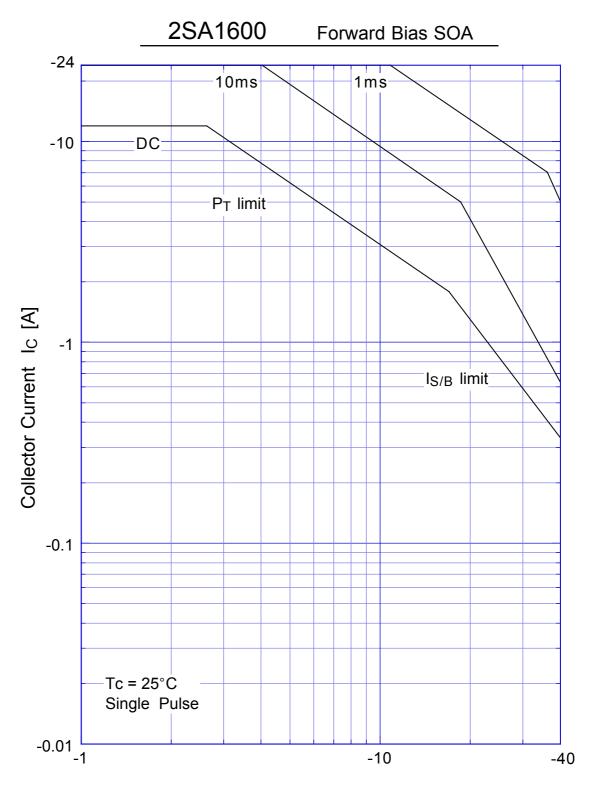


Base Current IB [A]









Collector-Emitter Voltage V_{CE} [V]

